Product data sheet

1. General description

NPN low V_{CEsat} transistor in a SOT457 (SC-74) small Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS302PD

2. Features and benefits

- Ultra low collector-emitter saturation voltage V_{CEsat}
- 4 A continuous collector current capability I_C
- · Up to 15 A peak current
- Very low collector-emitter saturation resistance
- · High efficiency due to less heat generation

3. Applications

- · Power management functions
- Charging circuits
- DC-to-DC conversion
- MOSFET gate driving
- Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base		-	-	40	V
I _C	collector current		[1]	-	-	4	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	15	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 6 A; I_B = 600 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C		-	55	75	mΩ

[1] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	С	collector		
2	С	collector	<u> </u>	C
3	В	base		В
4	Е	emitter		
5	С	collector	TSOP6 (SOT457)	E sym123
6	С	collector		5,25

6. Ordering information

Table 3. Ordering information

Type number Package					
	Name	Description	Version		
PBSS302ND	TSOP6	plastic, surface-mounted package (SC-74; TSOP6); 6 leads	SOT457		

7. Marking

Table 4. Marking codes

Type number	Marking code
	C7

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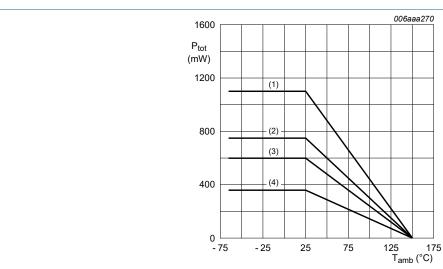
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	60	V
V _{CEO}	collector-emitter voltage	open base		-	40	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
I _C	collector current		[1]	-	4	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	15	Α
I _B	base current			-	0.8	Α
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	2	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	360	mW
			[3]	-	600	mW
			[4]	-	750	mW
			[1]	-	1.1	W
			[2] [5]	-	2.5	W
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm². Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm². [3]
- [4]
- [5] Operated under pulsed conditions: Duty cycle $\delta \le 10$ % and pulse width $t_p \le 10$ ms.



- (1) Ceramic PCB, Al_2O_3 , standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, mounting pad for collector 1 cm²
- (4) FR4 PCB, standard footprint

Power derating curves Fig. 1.

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	[2] [3] [4]	[1]	-	-	350	K/W
	junction to ambient		[2]	-	-	208	K/W
			[3]	-	-	167	K/W
			[4]	-	-	113	K/W
			[1] [5]	-	-	50	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	45	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm²
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [5] Operated under pulsed conditions: Duty cycle $\delta \le 10$ % and pulse width $t_p \le 10$ ms.

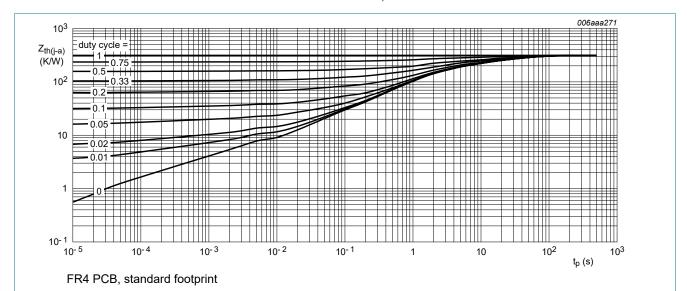


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

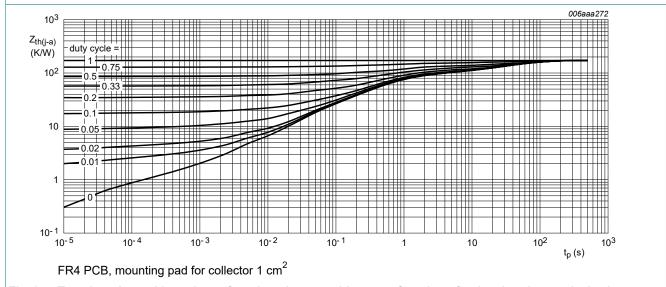
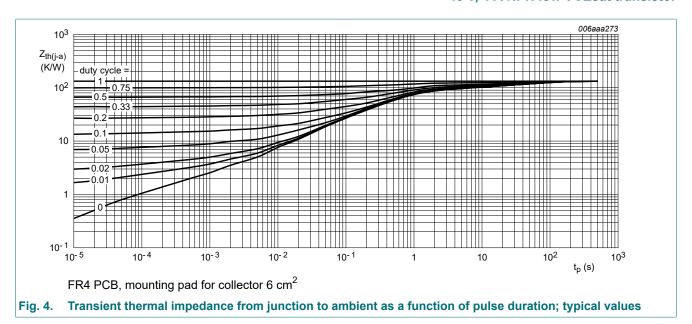


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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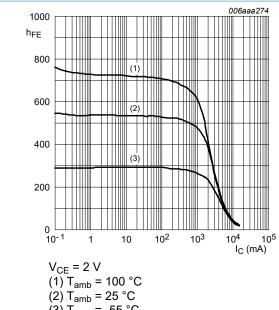
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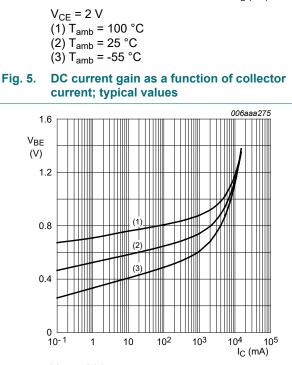
10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Сво	collector-base cut-off	V _{CB} = 40 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 40 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = 30 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 2 V; I _C = 0.5 A; T _{amb} = 25 °C	300	500	-	
		V_{CE} = 2 V; I_{C} = 1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	300	475	-	
		V_{CE} = 2 V; I_{C} = 2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	250	385	-	
		V_{CE} = 2 V; I_{C} = 4 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	100	190	-	
		V_{CE} = 2 V; I_{C} = 6 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	50	100	-	
V _{CEsat}	collector-emitter	I _C = 0.5 A; I _B = 50 mA; T _{amb} = 25 °C	-	35	60	mV
	saturation voltage	I _C = 1 A; I _B = 50 mA; T _{amb} = 25 °C	-	65	110	mV
		I _C = 2 A; I _B = 200 mA; T _{amb} = 25 °C	-	115	180	mV
		I_C = 4 A; I_B = 400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	220	300	mV
		$I_C = 6 \text{ A}$; $I_B = 600 \text{ mA}$; pulsed; $t_p \le$	-	330	450	mV
R _{CEsat}	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	55	75	mΩ
V _{BEsat}	base-emitter saturation voltage	I _C = 0.5 A; I _B = 50 mA; T _{amb} = 25 °C	-	0.79	0.85	V
		I _C = 1 A; I _B = 50 mA; T _{amb} = 25 °C	-	0.81	0.9	V
		I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.83	1	V
		I_C = 4 A; I_B = 400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	1	1.1	V
V_{BEon}	base-emitter turn-on voltage	V _{CE} = 2 V; I _C = 2 A; T _{amb} = 25 °C	-	0.79	1	V
t _d	delay time	$V_{CC} = 10 \text{ V}; I_C = 2 \text{ A}; I_{Bon} = 0.1 \text{ A};$	-	12	-	ns
t _r	rise time	I _{Boff} = -0.1 A; T _{amb} = 25 °C	-	52	-	ns
t _{on}	turn-on time		-	64	-	ns
t _s	storage time		-	390	-	ns
t _f	fall time		-	120	-	ns
t _{off}	turn-off time		-	510	-	ns
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 0.1 A; f = 100 MHz; T_{amb} = 25 °C	-	150	-	MHz
C _c	collector capacitance	V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	30	-	pF

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 $V_{CE} = 2 V$ (1) $T_{amb} = -55 °C$ (2) $T_{amb} = 25 °C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 7. Base-emitter voltage as a function of collector current; typical values

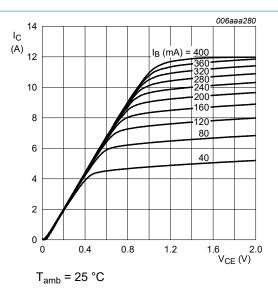
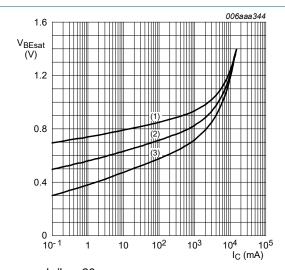


Fig. 6. Collector current as a function of collectoremitter voltage; typical values



 $I_C/I_B = 20$ (1) $T_{amb} = -55 \,^{\circ}C$ (2) $T_{amb} = 25 \,^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

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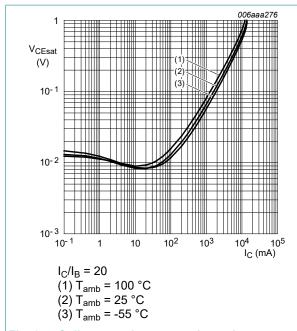


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

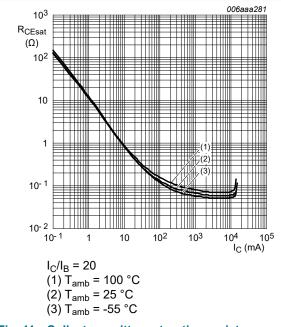


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

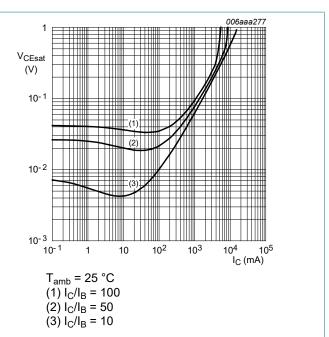


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

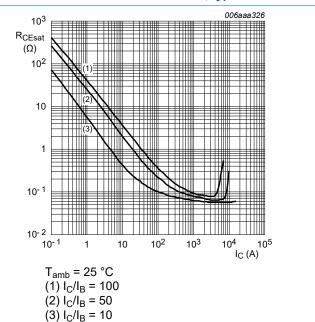
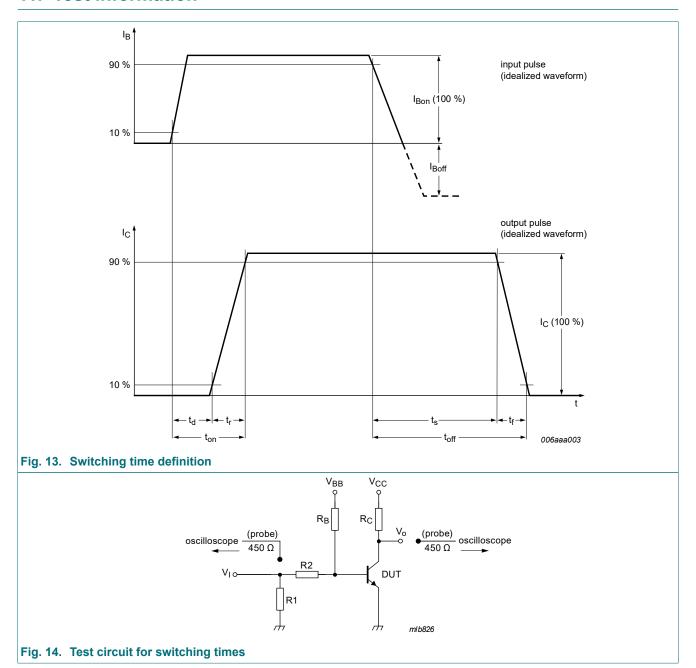


Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

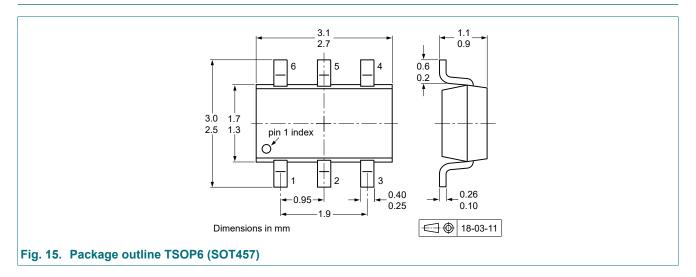
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11. Test information

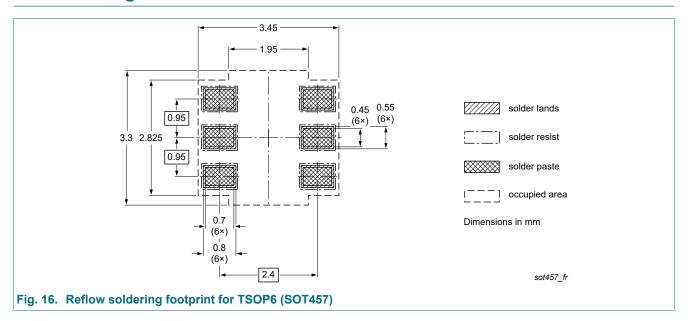


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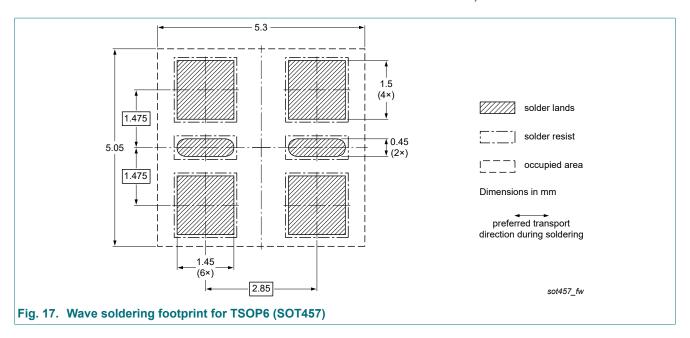
12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

Table 6. Revision history								
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PBSS302ND v.4	20241009	Product data sheet	-	PBSS302ND v.3				
Modifications:		Product(s) changed to non-automotive qualification. Please refer to nexperia.com for automotive (-Q) product alternative(s).						
PBSS302ND v.3	20230420	Product data sheet	-	PBSS302ND_2				
PBSS302ND_2	20080218	Product data sheet	-	PBSS302ND_1				
PBSS302ND_1	20050419	Product data sheet	-	-				

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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